

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-35 (canceled)

Claim 36 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion; and

transferring the device from the device holding layer onto a second substrate.

Claim 37 (previously presented): A method for transferring a device as claimed in claim 36, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 38 (previously presented): A method for transferring a device as claimed in claim 36, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 39 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 40 (previously presented): A method for transferring a device as claimed in claim 39, wherein the material is a nitride semiconductor material.

Claim 41 (previously presented): A method for transferring a device as claimed in claim 40, wherein the nitride semiconductor material is a GaN-based material.

Claim 42 (previously presented): A method for transferring a device as claimed in claim 36, wherein the first substrate is a sapphire substrate.

Claim 43 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device is a light-emitting device.

Claim 44 (previously presented): A method for transferring a device as claimed in claim 36, wherein the device holding layer is a silicone resin layer.

Claim 45 (previously presented): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion and a flat plate-shaped structure included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

Claim 46 (previously presented): A method for transferring a device as claimed in claim 45, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 47 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 48 (previously presented): A method for transferring a device as claimed in claim 47, wherein the material is a nitride semiconductor material.

Claim 49 (previously presented): A method for transferring a device as claimed in claim 48, wherein the nitride semiconductor material is a GaN-based material.

Claim 50 (previously presented): A method for transferring a device as claimed in claim 45, wherein the first substrate is a sapphire substrate.

Claim 51 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device is a light-emitting device.

Claim 52 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

Claim 53 (previously presented): A method for transferring a device as claimed in claim 45, wherein the device holding layer is a silicone resin layer.

Claims 54-74 (canceled)